

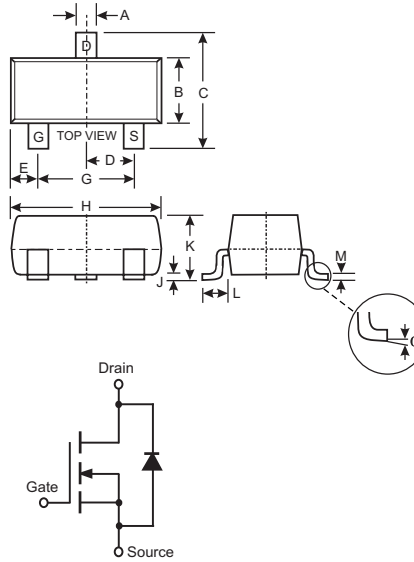
**N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR**

**Features**

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Available in Lead Free/RoHS Compliant Version (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

**Mechanical Data**

- Case: SOT-23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Also Available in Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe). Please see Ordering Information, Note 5, on Page 2
- Terminal Connections: See Diagram
- Marking (See Page 2): K38
- Ordering & Date Code Information: See Page 2
- Weight: 0.008 grams (approximate)



SOT-23		
Dim	Min	Max
A	0.37	0.51
B	1.20	1.40
C	2.30	2.50
D	0.89	1.03
E	0.45	0.60
G	1.78	2.05
H	2.80	3.00
J	0.013	0.10
K	0.903	1.10
L	0.45	0.61
M	0.085	0.180
$\alpha$	0°	8°
All Dimensions in mm		

**Maximum Ratings** @ T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	BSS138	Units
Drain-Source Voltage	V <sub>DSS</sub>	50	V
Drain-Gate Voltage R <sub>GS</sub> ≤ 20KΩ	V <sub>DGR</sub>	50	V
Gate-Source Voltage	V <sub>GSS</sub>	±20	V
Drain Current	I <sub>D</sub>	200	mA
Power Dissipation (Note 1)	P <sub>d</sub>	300	mW
Thermal Resistance, Junction to Ambient (Note 1)	R <sub>θJA</sub>	417	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** @ T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 2)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	50	75	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	0.5	μA	V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0V
Gate-Body Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 2)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.5	1.2	1.5	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	1.4	3.5	Ω	V <sub>GS</sub> = 10V, I <sub>D</sub> = 0.22A
Forward Transconductance	g <sub>FS</sub>	100	—	—	mS	V <sub>DS</sub> = 25V, I <sub>D</sub> = 0.2A, f = 1.0KHz
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	C <sub>iSS</sub>	—	—	50	pF	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	—	25	pF	
Reverse Transfer Capacitance	C <sub>rSS</sub>	—	—	8.0	pF	
<b>SWITCHING CHARACTERISTICS</b>						
Turn-On Delay Time	t <sub>D(ON)</sub>	—	—	20	ns	V <sub>DD</sub> = 30V, I <sub>D</sub> = 0.2A, R <sub>GEN</sub> = 50Ω
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	—	20	ns	

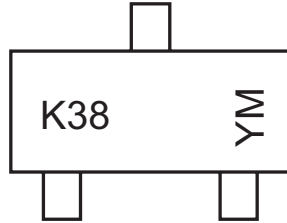
- Notes:
1. Device mounted on FR-5 PCB 1.0 x 0.75 x 0.062 inch pad layout as shown on Diodes, Inc. suggested pad layout AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
  2. Short duration test pulse used to minimize self-heating effect.
  3. No purposefully added lead.

**Ordering Information** (Note 4)

Device	Packaging	Shipping
BSS138-7	SOT-23	3000/Tape & Reel

- Notes: 4. For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.  
5. For Lead Free/RoHS Compliant version part number, please add "-F" suffix to the part number above. Example: BSS138-7-F.

**Marking Information**



K38 = Product Type Marking Code  
YM = Date Code Marking  
Y = Year ex: N = 2002  
M = Month ex: 9 = September

Date Code Key

Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009
Code	J	K	L	M	N	P	R	S	T	U	V	W

Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

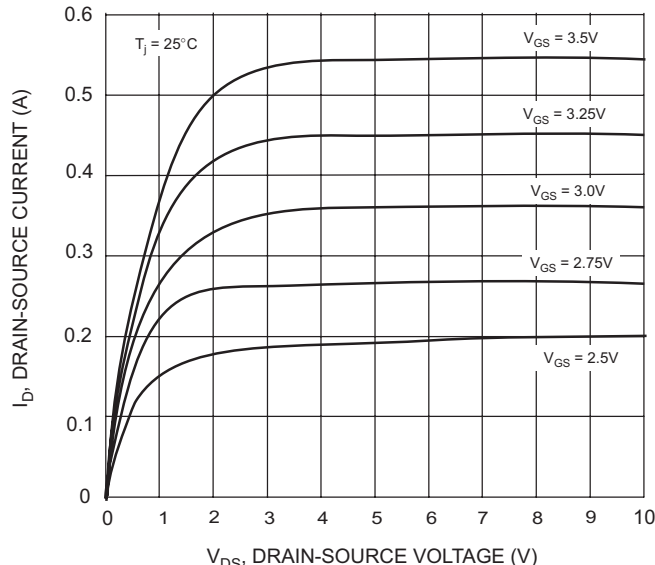


Fig. 1 Drain-Source Current vs. Drain-Source Voltage

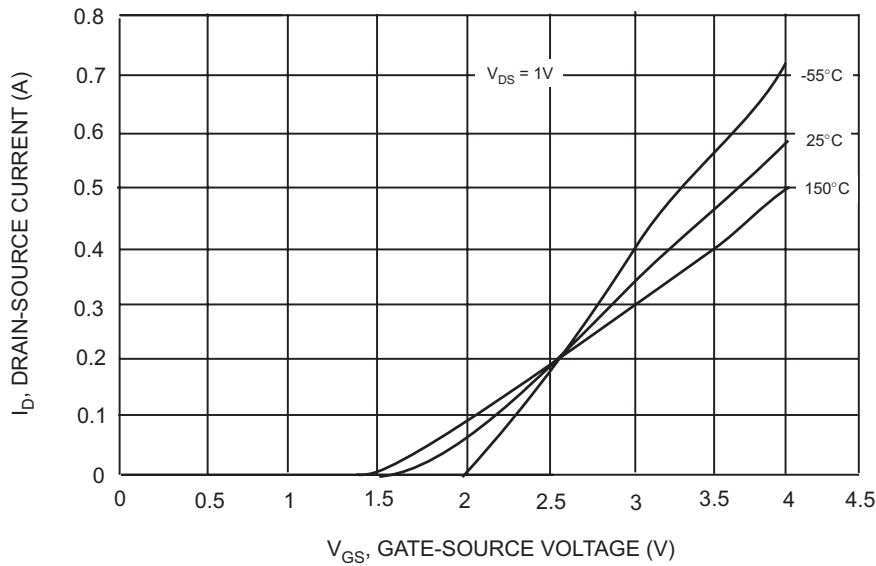


Fig. 2 Transfer Characteristics

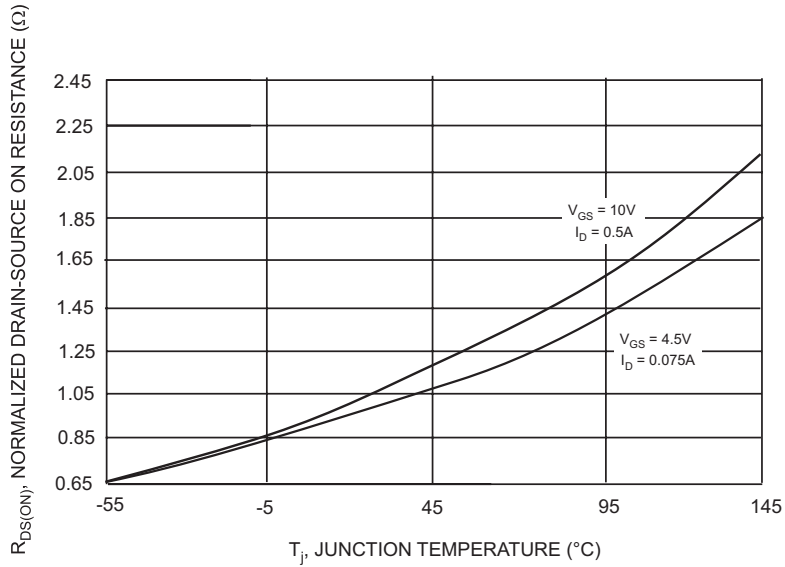


Fig. 3 Drain-Source On Resistance vs. Junction Temperature

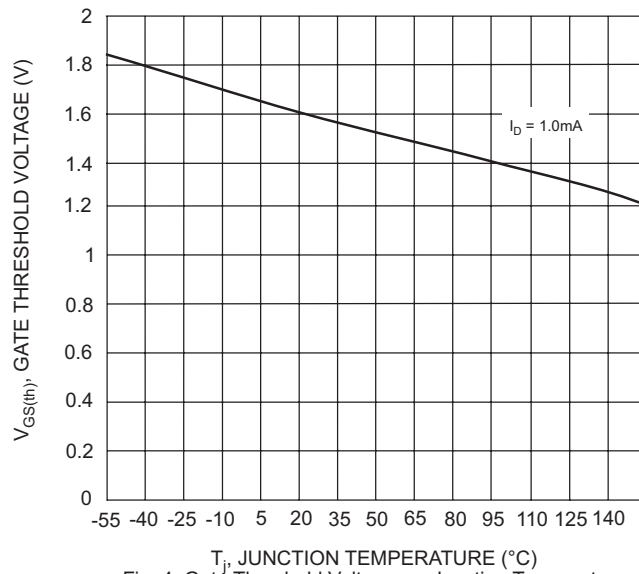


Fig. 4 Gate Threshold Voltage vs. Junction Temperature

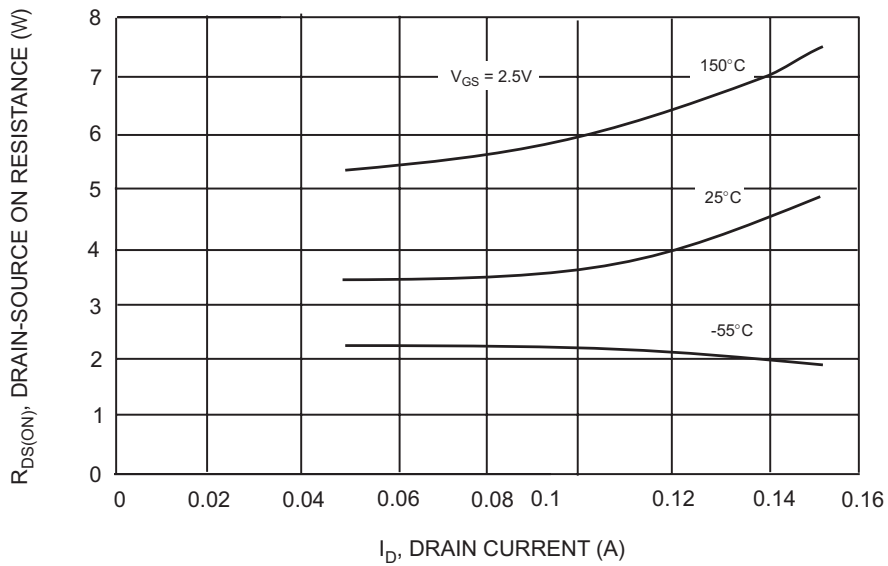


Fig. 5 Drain-Source On Resistance vs. Drain Current

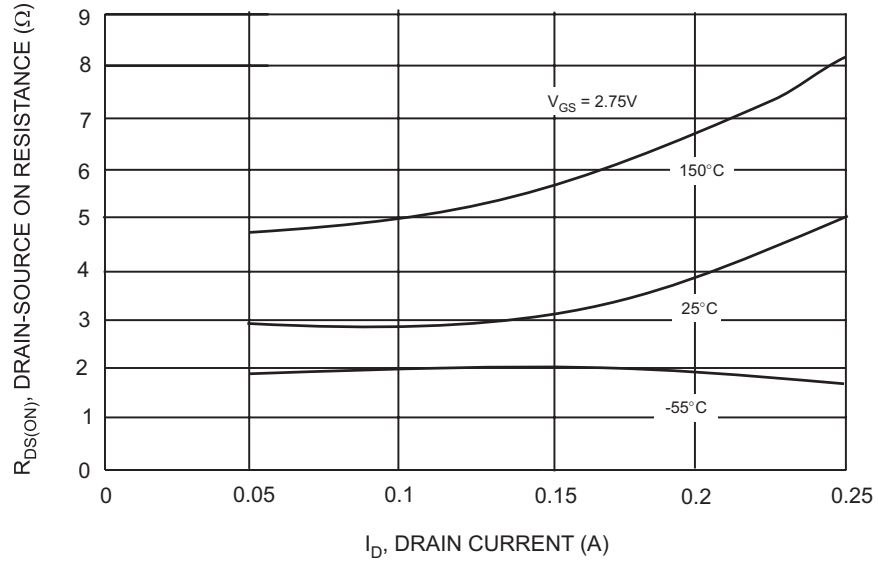


Fig. 6 Drain-Source On Resistance vs. Drain Current

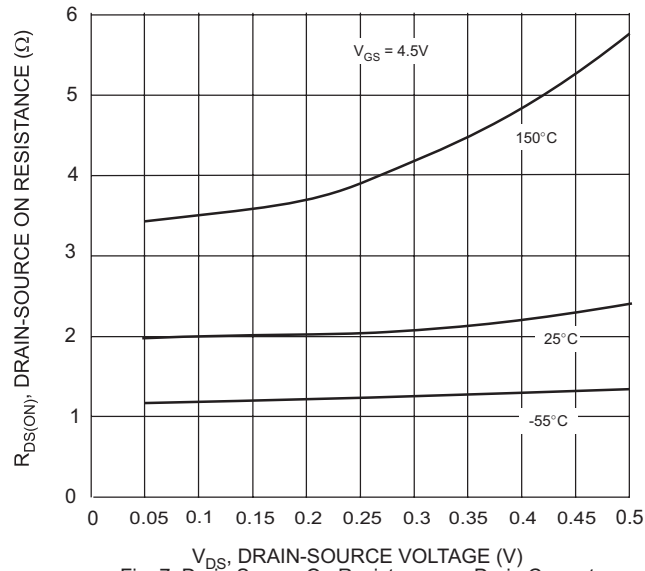


Fig. 7 Drain-Source On Resistance vs. Drain Current

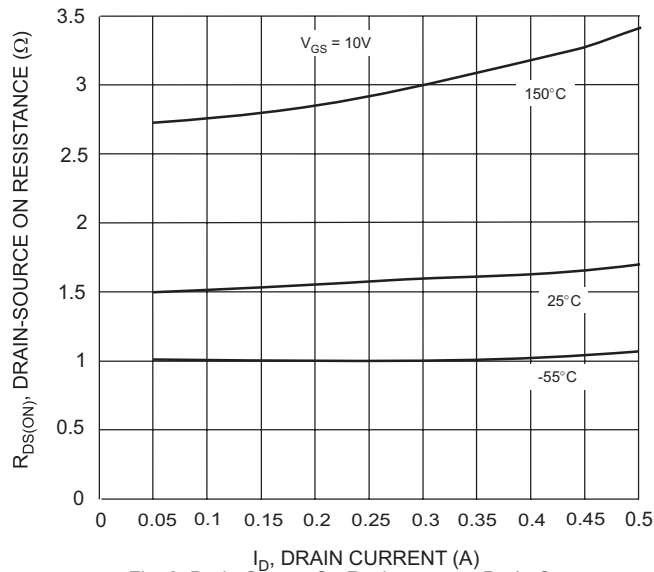


Fig. 8 Drain-Source On Resistance vs. Drain Current

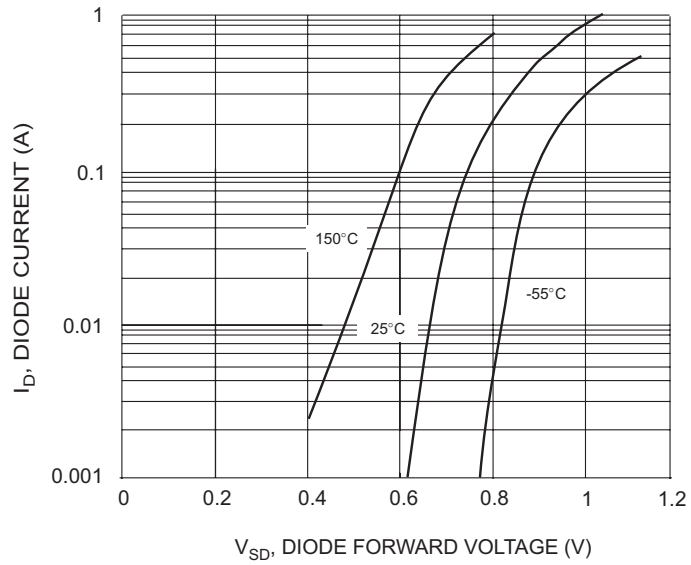


Fig. 9 Body Diode Current vs. Body Diode Voltage

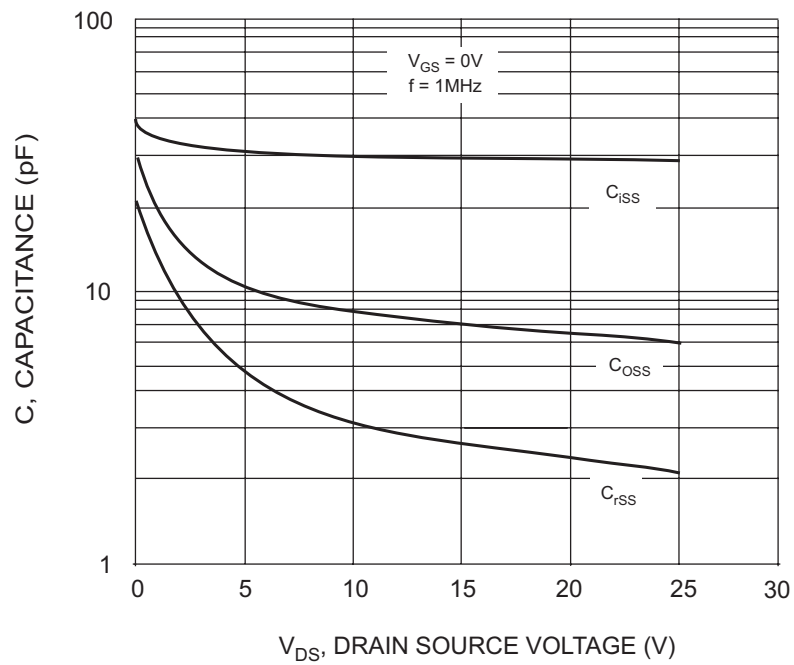


Fig. 10 Capacitance vs. Drain Source Voltage